



P-Channel 20-V (G-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^c	Q _g (Typ.)
- 20	0.080 at V _{GS} = - 10 V	- 2.7	5.5 nC
	0.100 at V _{GS} = - 4.5 V	- 2.7	
	0.155 at V _{GS} = - 2.5 V	- 2.7	

FEATURES

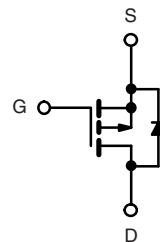
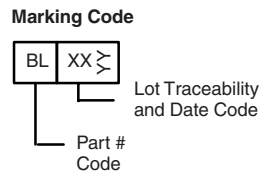
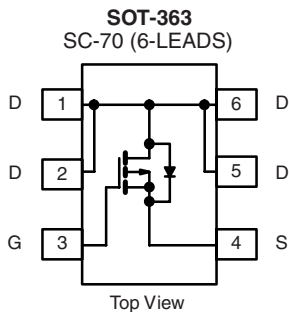
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT

APPLICATIONS

- Load Switch for Portable Devices



P-Channel MOSFET

Ordering Information: Si1469DH-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 20	V
Gate-Source Voltage	V _{GS}	± 12	
Continuous Drain Current (T _J = 150 °C) ^{a, b}	I _D	T _C = 25 °C	- 2.7 ^c
		T _C = 70 °C	- 2.7 ^c
		T _A = 25 °C	- 3.2 ^{a, b}
		T _A = 70 °C	- 2.6 ^{a, b}
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	- 8	A
Continuous Source-Drain Diode Current ^{a, b}	I _S	T _C = 25 °C	
		T _A = 25 °C	- 1.25 ^{a, b}
Maximum Power Dissipation ^{a, b}	P _D	T _C = 25 °C	2.78
		T _C = 70 °C	1.78
		T _A = 25 °C	1.5 ^{a, b}
		T _A = 70 °C	1 ^{a, b}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{c, d}		260	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, d}	R _{thJA}	60	80	°C/W
Maximum Junction-to-Foot (Drain)	R _{thJF}	34	45	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. t = 5 s.

c. Package limited.

d. Maximum under Steady State conditions is 125 °C/W.



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-21		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-2.4		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.6		-1.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			-100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = -4.5\text{ V}$	-3			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -2.0\text{ A}$		0.065	0.080	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -1.8\text{ A}$		0.081	0.100	
		$V_{GS} = -2.5\text{ V}, I_D = -1.5\text{ A}$		0.126	0.155	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -2.0\text{ A}$		6		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		470		μF
Output Capacitance	C_{oss}			105		
Reverse Transfer Capacitance	C_{rss}			80		
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$		5.5	8.5	nC
Gate-Source Charge	Q_{gs}			0.8		
Gate-Drain Charge	Q_{gd}			1.7		
Gate Resistance	R_g	$f = 1\text{ MHz}$		10		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 5\text{ }\Omega$ $I_D \cong -2\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		27	41	ns
Rise Time	t_r			48	72	
Turn-Off Delay Time	$t_{d(off)}$			27	41	
Fall Time	t_f			15	23	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 5\text{ }\Omega$ $I_D \cong -2\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		5	10	
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			22	33	
Fall Time	t_f			9	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-1.6	A
Pulse Diode Forward Current	I_{SM}				-6.5	
Body Diode Voltage	V_{SD}	$I_S = -2\text{ A}, V_{GS} = 0\text{ V}$		-0.83	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -2.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		20	30	ns
Body Diode Reverse Recovery Charge	Q_{rr}			8	15	nC
Reverse Recovery Fall Time	t_a			7		ns
Reverse Recovery Rise Time	t_b			13		

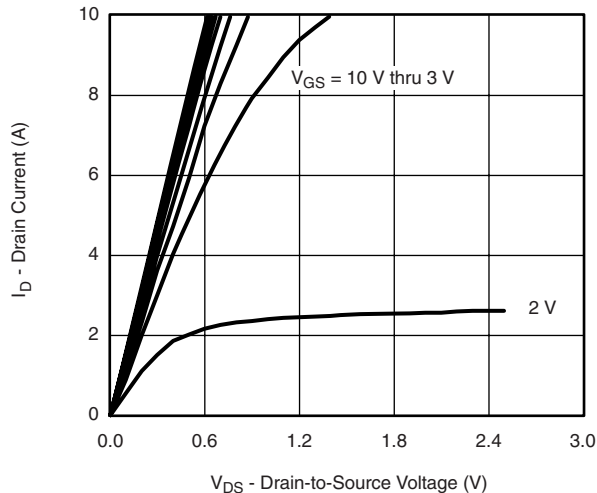
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

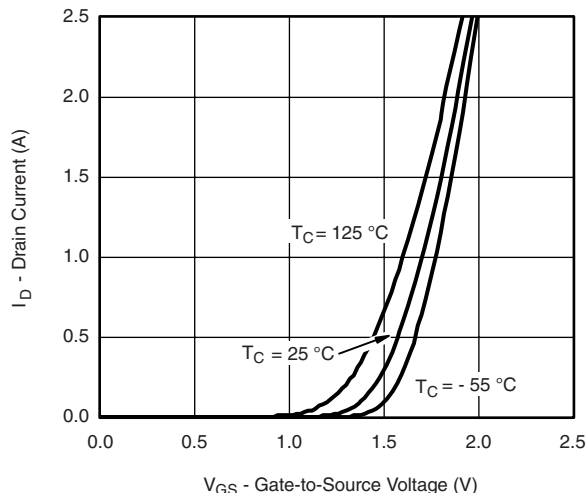
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



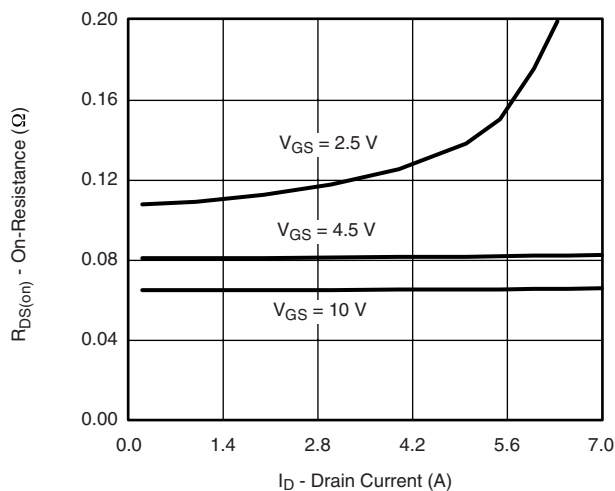
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



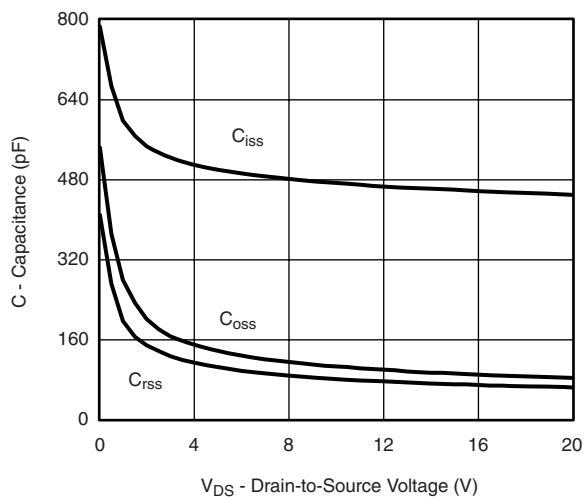
Output Characteristics



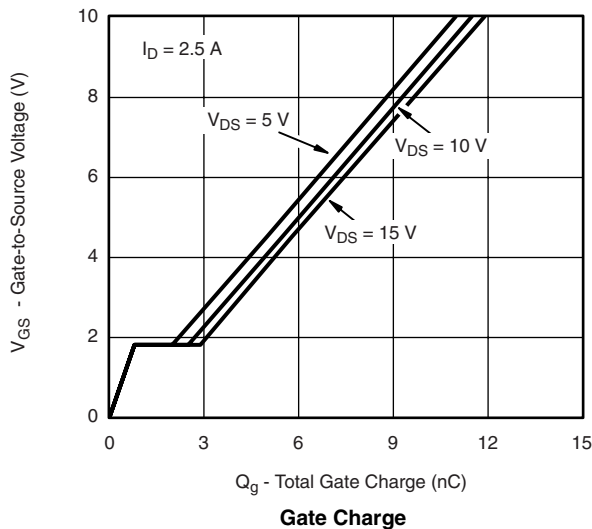
Transfer Characteristics



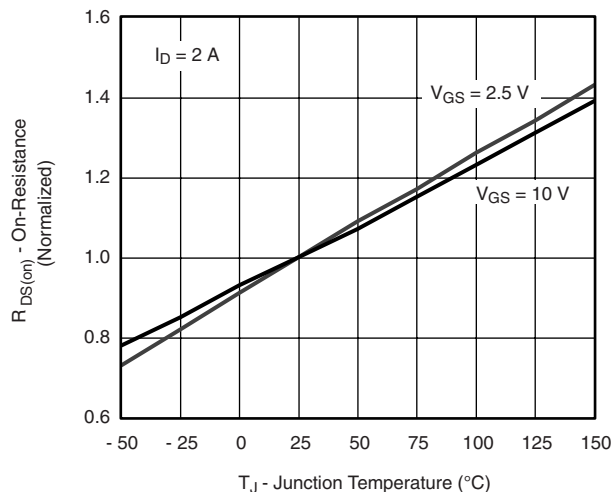
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



Gate Charge



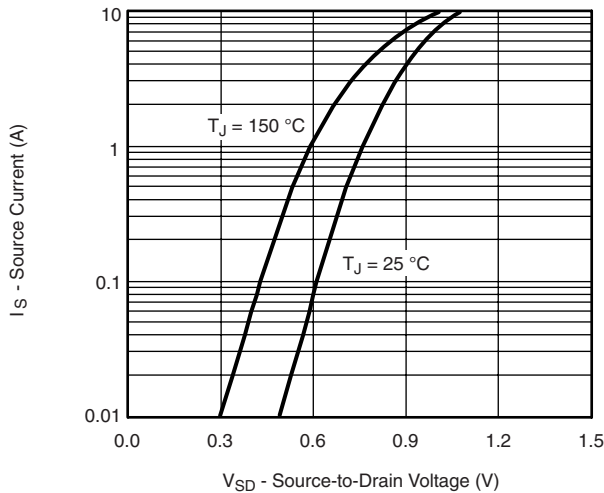
On-Resistance vs. Junction Temperature

Si1469DH

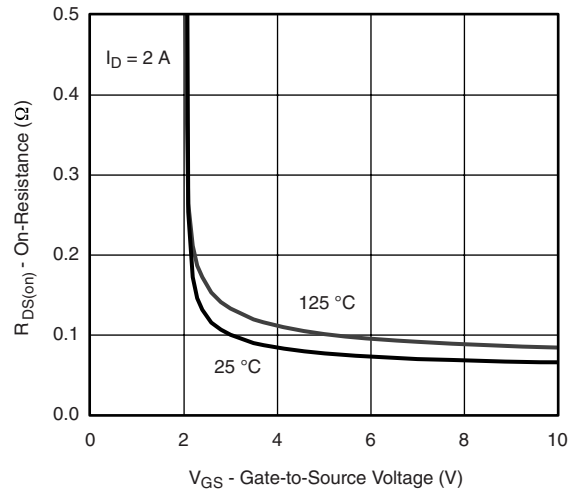
Vishay Siliconix



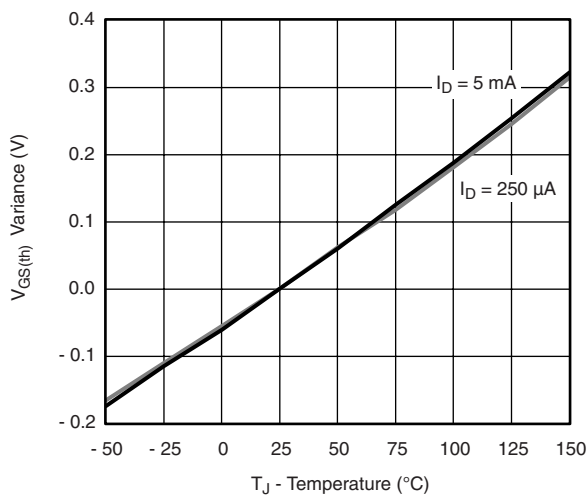
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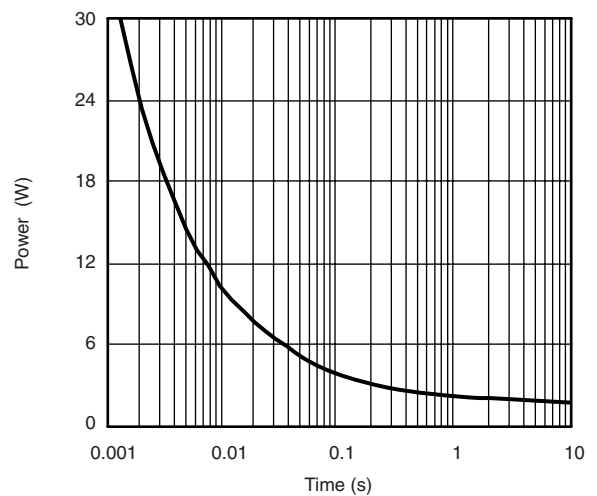
Source-Drain Diode Forward Voltage



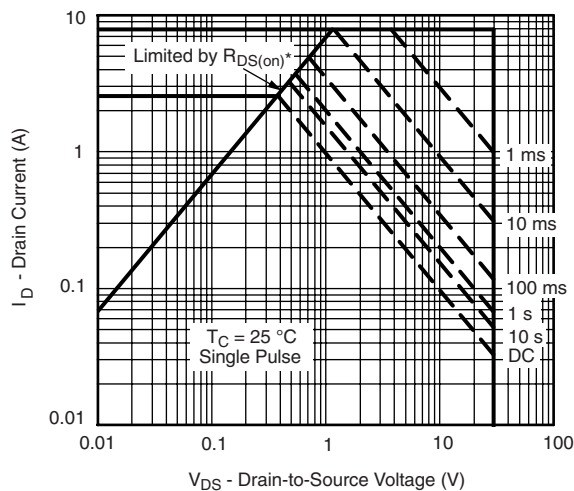
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

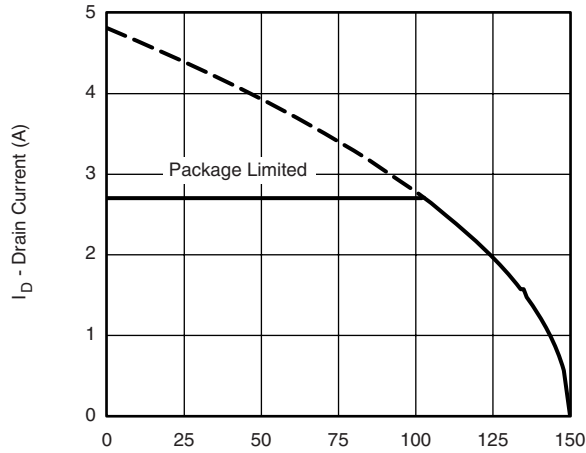


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

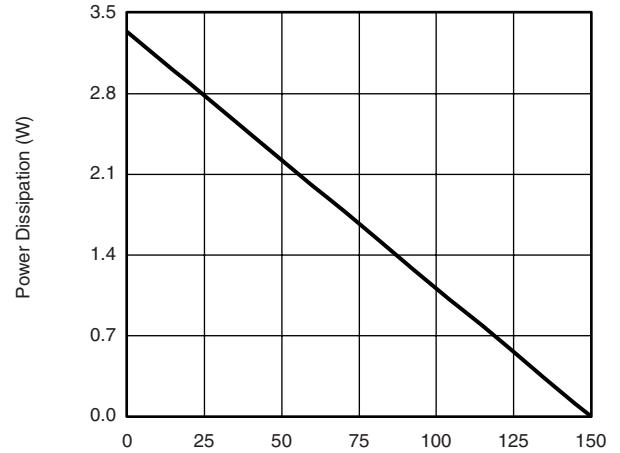
Safe Operating Area, Junction-to-Ambient



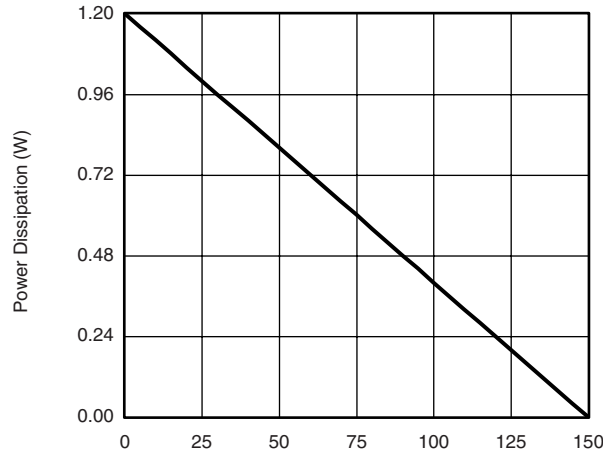
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



T_C - Case Temperature (°C)
Current Derating*



T_C - Case Temperature (°C)
Power Derating, Junction-to-Foot



T_A - Ambient Temperature (°C)
Power Derating, Junction-to-Ambient

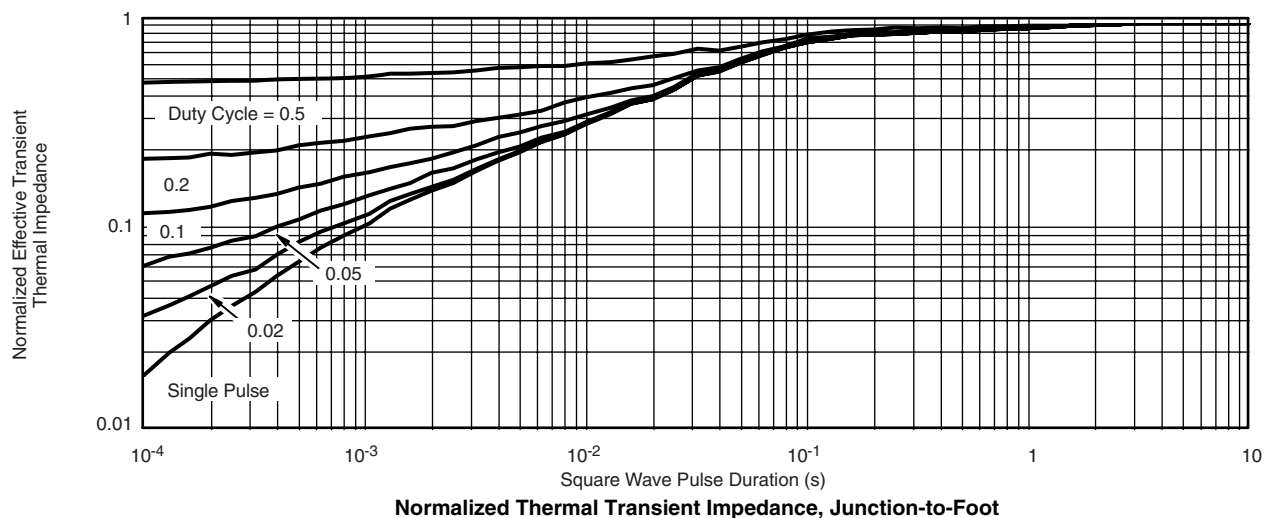
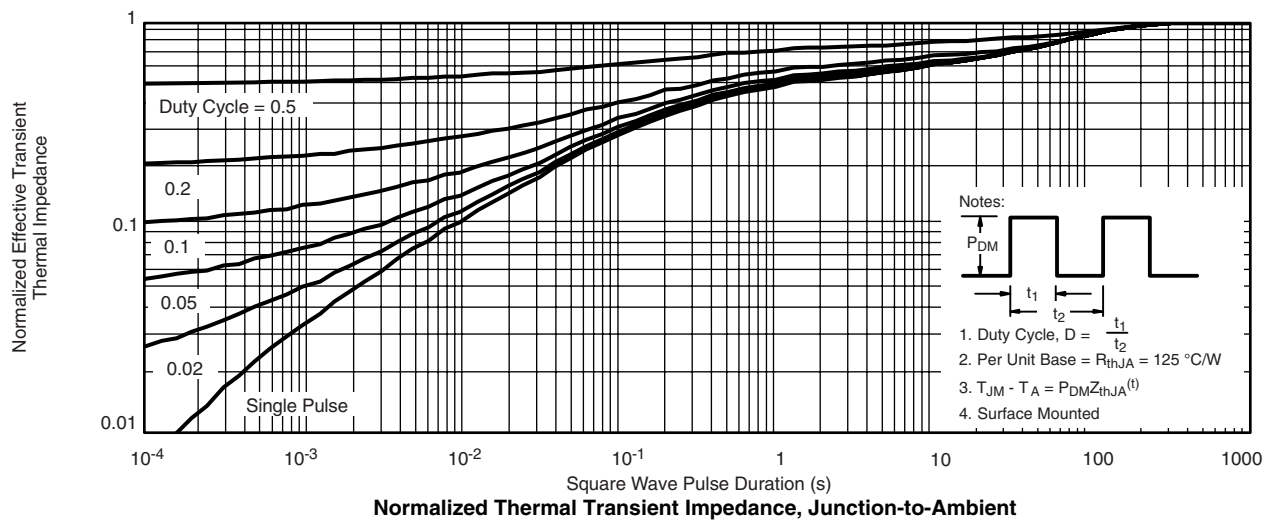
* The power dissipation P_D is based on T_{J(max)} = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si1469DH

Vishay Siliconix



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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